7/8/03 10/613,997

SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION PTO-1449	26615 PATENT TRADEMARK OFFICE	ATTORNEY'S DKT NO. H1131	APPLICATION NO. ~~Unassigned~~ 10/613997
		APPLICANT(S) Matthew S. BUYNOSKI et al.	
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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
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EXAMINER	Michael Trinh	DATE CONSIDERED	12/8/03

EXAMINER: *Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).*